Amendments to the claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (ORIGINAL) A method for producing Group-III-element nitride single crystal, comprising:

reacting at least one Group III element selected from the group consisting of gallium (Ga), aluminum (Al), and indium (In) with nitrogen (N) in a mixed flux containing sodium (Na) and at least one of an alkali metal (other than Na) and an alkaline-earth metal, thereby causing Group-III-element nitride single crystal to grow.

2. (CURRENTLY AMENDED) The method according to claim 1, wherein the Group III element is gallium (Ga), and the Group-III-element nitride single crystal is gallium ~~(Ga)~~ nitride (GaN) single crystal.

3. (CURRENTLY AMENDED) The method according to claim 1, wherein the ~~alkali metal is at least one selected from the group consisting of lithium (Li), potassium (K), rubidium (Rb), cesium (Cs), and francium (Fr), and the alkaline-earth metal is at least one selected from the group consisting of calcium (Ca), strontium (Sr), barium (Br), and radium (Ra)~~ mixed flux is a mixed flux of sodium (Na) and calcium (Ca).

4. (CURRENTLY AMENDED) The method according to claim 1, wherein the mixed flux is a mixed flux of sodium (Na) and ~~calcium~~ lithium (Li).

5. (CURRENTLY AMENDED) The method according to ~~claim 4~~ claim 1, wherein ~~a ratio of the calcium (Ca) to the total of the sodium (Na) and the calcium (Ca) is in a range from 0.1 to 99 mol%~~ the mixed flux is a mixed flux of sodium (Na), calcium (Ca), and lithium (Li).

6. (CURRENTLY AMENDED) The method according to claim 1, wherein ~~the mixed flux is a mixed flux of sodium (Na) and lithium (Li)~~ the reaction is carried out under conditions of a temperature of 100°C to 1200°C and a pressure of 100 Pa to 200 MPa.

7. (CURRENTLY AMENDED) The method according to ~~claim 6~~ claim 1, wherein ~~a ratio of the lithium (Li) to the total of the sodium (Na) and the lithium is in a range from 0.1 to 99 mol%~~ nitrogen (N) containing gas is used as a nitrogen source.

8. (CURRENTLY AMENDED) The method according to ~~claim 1~~ claim 7, wherein the ~~reaction is carried out under conditions of a temperature of 100°C to 1200°C and a pressure of 100 Pa to 200 MPa~~ nitrogen (N) containing gas is at least one selected from the group consisting of nitrogen (N_2) gas, ammonia (NH_3) gas, and a mixed gas containing the nitrogen (N_2) gas and the ammonia (NH_3) gas.

9. (CURRENTLY AMENDED) The method according to claim 1, wherein ~~nitrogen (N) containing gas is used as a nitrogen source~~ the single crystal is transparent.

10. (CURRENTLY AMENDED) The method according to ~~claim 9~~ claim 1, wherein ~~the nitrogen (N) containing gas is at least one of nitrogen (N_2) gas and ammonia (NH_3) gas~~ a Group-

III-element nitride is provided beforehand, and the Group-III-element nitride is brought into contact with the mixed flux to cause new Group-III-element nitride single crystal to grow using the Group-III-element nitride as a nucleus.

11. (CURRENTLY AMENDED) The method according to ~~claim 9~~ claim 10, wherein the ~~nitrogen (N) containing gas is ammonia (NH_3) gas or a mixed gas containing the ammonia (NH_3) gas and nitrogen (N) gas~~ the Group-III-element nitride that serves as the nucleus is single crystal or amorphous.

12. (CURRENTLY AMENDED) The method according to ~~claim 1~~ claim 10, wherein ~~a Group-III-element nitride is provided beforehand, and the Group-III-element nitride is brought into contact with the mixed flux to cause new Group-III-element nitride single crystal to grow using the Group-III-element nitride as a nucleus~~ the Group-III-element nitride that serves as the nucleus is in a form of a thin film.

13. (CURRENTLY AMENDED) The method according to claim 12, wherein the ~~Group-III-element nitride that serves as the nucleus is single crystal or amorphous~~ thin film is formed on a substrate.

14. (CURRENTLY AMENDED) The method according to ~~claim 12~~ claim 10, wherein ~~the Group-III-element nitride that serves as the nucleus is in a form of a thin film~~ a nitride is present in the mixed flux at least at an initial stage of the reaction.

15. (CURRENTLY AMENDED) The method according to claim 14, wherein the ~~thin film is formed on a substrate~~ nitride is at least one selected from the group consisting of Ca_3N_2, Li_3N, NaN_3, BN, Si_3N_4, and InN.

16. (ORIGINAL) The method according to claim 1, wherein the mixed flux contains an impurity as a dopant.

17. (ORIGINAL) The method according to claim 16, wherein the impurity is at least one selected from the group consisting of carbon (C), oxygen (O), silicon (Si), alumina (Al_2O_3), indium (In), aluminum (Al), indium nitride (InN), silicon oxide (SiO_2), indium oxide (In_2O_3), zinc (Zn), magnesium (Mg), zinc oxide (ZnO), magnesium oxide (MgO), and germanium (Ge).

18. (CURRENTLY AMENDED) ~~The method according to claim 1, which causes transparent single crystal to grow~~ Group-III-element nitride single crystal obtained by the method according to claim 1.

19. (CURRENTLY AMENEDED) ~~A method for producing Group-III-element nitride single crystal, comprising: reacting at least one Group III element selected from the group consisting of gallium (Ga), aluminum (Al), and indium (In) with nitrogen (N) in a metal flux containing at least one of an alkali metal and an alkaline-earth metal, thereby causing Group-III-element nitride single crystal to grow,~~

~~wherein a Group-III-element nitride is provided beforehand, and the Group-III-element nitride is brought into contact with the metal flux to cause new Group-III-element nitride single~~

~~crystal to grow using the Group-III-element nitride as a nucleus~~ Gallium nitride (GaN) single crystal obtained by the method according to claim 2.

20. (CURRENTLY AMENDED) ~~The method according to claim 19, wherein the Group III element is gallium (Ga), and the Group-III-element nitride single crystal is gallium (Ga) nitride single crystal~~ A semiconductor device comprising the Group-III-element nitride single crystal according to claim 18.

21. - 60. (CANCELLED)